Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	467	(high adj density) and (plasma with oxidation) and ((silicon adj carbide) or SiC)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 14:04
S2	24	S1 and (oxygen with plasma) and inductive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 15:24
S3	1	("5891349").PN.	USPAT	OR	OFF	2006/01/12 13:52
S4	0	(high adj density) and HDPECvD and (top adj electrode) and (bottom adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 14:06
S5	321	(high adj density) and PECvD and (top adj electrode) and (bottom adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 14:08
S6	7	S5 and (plasma with oxidation) and SiC	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 14:07
S7	68	((high adj density) with PECvD) and (top adj electrode) and (bottom adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 14:12
S8	298	PECvD adj apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 14:13
S9	0	S8 and (high adj density) and (top adj electrode) and (bottom adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 14:14

S10	1	S8 and (high adj density) and (top adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 14:15
S11	42	S8 and ((high adj density) with plasma) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 16:04
S12	1851	plasma with oxidation with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 16:20
S13	48	S12 and "SiH.sub.4" and "N.sub.2O" and "N.sub.2"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 17:03
S14	23	S12 and ((bias with temperature with stress) or BTS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 16:27
S15	1622	(silicon with oxide) and ((bias with temperature with stress) or BTS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/12 16:28
S16	5	(silicon with oxide) and ((bias with temperature with stress) or BTS) and (breakdown with strength) and (leakage with current with density)	USPAT	OR	ON	2006/01/12 16:28
S17	4	("4585668"|"6149987"|"6794242"|"6900138").PN.	US-PGPUB; USPAT	OR	ON	2006/01/12 17:03
S18	29	(SiC with FET) and (Schottky with gate)	USPAT	OR	ON	2006/01/13 15:29
S19	21	S18 and (SiC with substrate)	USPAT	OR	ON	2006/01/13 15:29
S20	3	("6136727"|"6437371"|"6482704").PN.	US-PGPUB; USPAT	OR	ON	2006/01/16 15:57
S21	2832	438/758,762,765,767,769,770-772,787.ccls.	US-PGPUB; USPAT	OR	ON	2006/01/16 15:58

S22		23	S21 and (((silicon adj carbide) or SiC) with substrate) and (plasma with oxidation)	US-PGPUB; USPAT	OR	ON	2006/01/16 15:59